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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

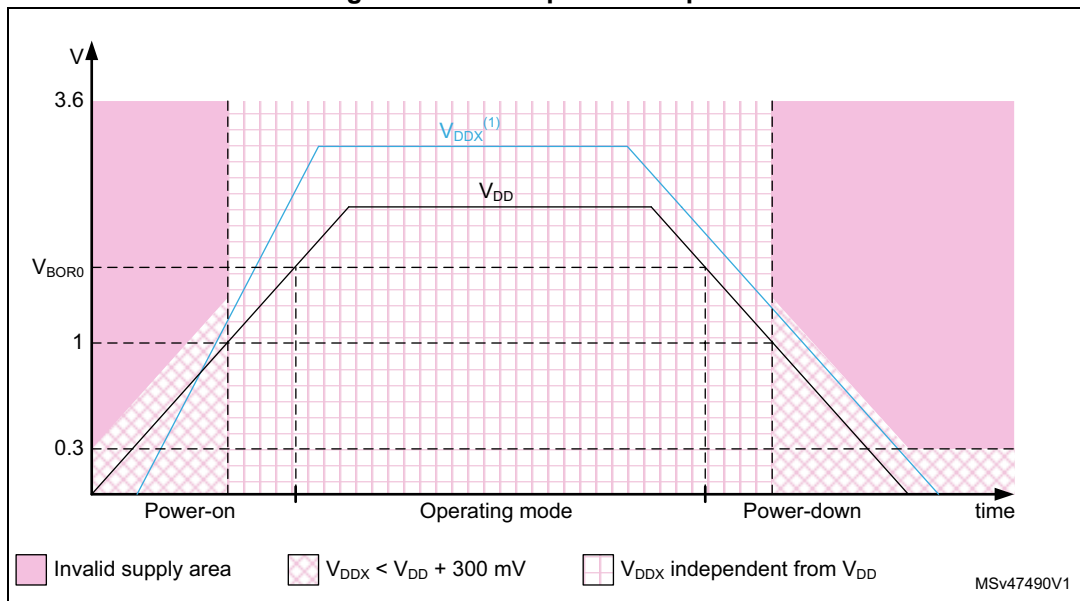
Applications of "[Embedded - Microcontrollers](#)"

Details

Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	120MHz
Connectivity	CANbus, EBI/EMI, I ² C, IrDA, LINbus, MMC/SD, SAI, SPI, UART/USART, USB OTG
Peripherals	Brown-out Detect/Reset, DMA, LCD, POR, PWM, WDT
Number of I/O	112
Program Memory Size	2MB (2M x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	640K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 3.6V
Data Converters	A/D 16x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l4s9zit6

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Figure 5. Power-up/down sequence



1. V_{DDX} refers to any power supply among V_{DDA} , V_{DDIO2} , V_{DDUSB} and V_{LCD} .

3.10.2 Power supply supervisor

The STM32L4S5xx, STM32L4S7xx and STM32L4S9xx devices have an integrated ultra-low-power Brownout reset (BOR) active in all modes (except for Shutdown mode). The BOR ensures proper operation of the devices after power-on and during power-down. The devices remain in reset mode when the monitored supply voltage V_{DD} is below a specified threshold, without the need for an external reset circuit.

The lowest BOR level is 1.71 V at power on, and other higher thresholds can be selected through option bytes. The devices feature an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the VPVD threshold.

An interrupt can be generated when V_{DD} drops below the VPVD threshold and/or when V_{DD} is higher than the VPVD threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

In addition, the devices embed a peripheral voltage monitor which compares the independent supply voltages V_{DDA} , V_{DDUSB} , V_{DDIO2} with a fixed threshold in order to ensure that the peripheral is in its functional supply range.

3.10.3 Voltage regulator

Two embedded linear voltage regulators supply most of the digital circuitries: the main regulator (MR) and the low-power regulator (LPR).

- The MR is used in the Run and Sleep modes and in the Stop 0 mode.
- The LPR is used in Low-power run, Low-power sleep, Stop 1 and Stop 2 modes. It is also used to supply the 64 Kbytes SRAM2 in standby with RAM2 retention.
- Both regulators are in power-down while they are in standby and Shutdown modes: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

interrupt is generated if enabled. LSE failure can also be detected and generated an interrupt.

- Clock-out capability:
 - **MCO (microcontroller clock output)**: it outputs one of the internal clocks for external use by the application
 - **LSCO (low-speed clock output)**: it outputs LSI or LSE in all low-power modes (except VBAT).

Several prescalers allow to configure the AHB frequency, the high speed APB (APB2) and the low-speed APB (APB1) domains. The maximum frequency of the AHB and the APB domains is 120 MHz.

3.15 DMA request router (DMAMux)

When a peripheral indicates a request for DMA transfer by setting its DMA request line, the DMA request is pending until it is served and the corresponding DMA request line is reset. The DMA request router allows to route the DMA control lines between the peripherals and the DMA controllers of the product.

An embedded multi-channel DMA request generator can be considered as one of such peripherals. The routing function is ensured by a multi-channel DMA request line multiplexer. Each channel selects a unique set of DMA control lines, unconditionally or synchronously with events on synchronization inputs.

For simplicity, the functional description is limited to DMA request lines. The other DMA control lines are not shown in figures or described in the text. The DMA request generator produces DMA requests following events on DMA request trigger inputs.

3.16 Chrom-ART Accelerator™ (DMA2D)

Chrom-ART Accelerator™ (DMA2D) is a graphic accelerator that offers an advanced bit blitting, row data copy and pixel format conversion. It supports the following functions:

- Rectangle filling with a fixed color
- Rectangle copy
- Rectangle copy with pixel format conversion
- Rectangle composition with blending and pixel format conversion.

Various image format coding are supported, from indirect 4 bpp color mode up to 32 bpp direct color. It embeds a dedicated memory to store color lookup tables.

An interrupt can be generated when an operation is complete or at a programmed watermark.

All the operations are fully automatized and are running independently from the CPU or the DMAs.

3.17 Chrom-GRC™ (GFXMMU)

The Chrom-GRC™ (GFXMMU) is a graphical oriented memory management unit aimed to:

- Optimize memory usage according to the display shape
- Manage packing/unpacking for 24 bpp frame buffers

The Chrom-GRC™ features:

- Fully programmable display shape to physically store only the visible pixel
- Up to four virtual buffers
- Each virtual buffer have 4096 bytes per line and 1024 lines
- Each virtual buffer can be physically mapped to any system memory
- 24 bpp packing unit to store unpacked 24bpp data in a packed 24 bpp
- Packing/un-packing management per buffer
- Interrupt in case of buffer overflow (1 per buffer)
- Interrupt in case of memory transfer error

Table 15. STM32L4Sxxx pin definitions

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4S5xx STM32L4S7xx					STM32L4S9xx										
LQFP100	BGA132	LQFP144	WLCSP144	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144	UFBGA169						
-	-	-	-	M11	-	-	-	-	M11	VSS	S	-	-	-	-
-	-	-	-	C1	-	-	-	-	C1	VDD	S	-	-	-	-
-	-	-	-	C3	-	-	-	-	C3	PI11	I/O	FT	-	OCTOSPIM_P2_IO0 , EVENTOUT	-
1	B2	1	B11	D3	1	1	C3	B11	D3	PE2	I/O	FT_I	-	TRACECK, TIM3_ETR, SAI1_CK1, TSC_G7_IO1, LCD_R0, FMC_A23, SAI1_MCLK_A, EVENTOUT	-
2	A1	2	C11	D2	2	2	B3	C11	D2	PE3	I/O	FT_I	-	TRACED0, TIM3_CH1, OCTOSPIM_P1_DQ S, TSC_G7_IO2, LCD_R1, FMC_A19, SAI1_SD_B, EVENTOUT	-
3	B1	3	C12	D1	3	3	D3	C12	D1	PE4	I/O	FT	-	TRACED1, TIM3_CH2, SAI1_D2, DFSDM1_DATIN3, TSC_G7_IO3, DCMI_D4, LCD_B0, FMC_A20, SAI1_FS_A, EVENTOUT	-
4	C2	4	D9	E4	4	4	C2	D9	E4	PE5	I/O	FT	-	TRACED2, TIM3_CH3, SAI1_CK2, DFSDM1_CKIN3, TSC_G7_IO4, DCMI_D6, LCD_G0, FMC_A21, SAI1_SCK_A, EVENTOUT	-
5	D2	5	D10	E3	5	5	D4	D10	E3	PE6	I/O	FT	-	TRACED3, TIM3_CH4, SAI1_D1, DCMI_D7, LCD_G1, FMC_A22, SAI1_SD_A, EVENTOUT	RTC_TAMP3, WKUP3
6	E2	6	E10	E2	6	6	B1	E10	E2	VBAT	S	-	-	-	-

Table 15. STM32L4Sxxx pin definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4S5xx STM32L4S7xx					STM32L4S9xx										
LQFP100	BGA132	LQFP144	WLCSP144	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144	UFBGA169						
18	K2	29	J10	K1	18	27	J3	J10	K1	PC3	I/O	FT_a	-	LPTIM1_ETR, SAI1_D1, SPI2_MOSI, OCTOSPIM_P1_IO6 , SAI1_SD_A, LPTIM2_ETR, EVENTOUT	ADC1_IN4
19	-	30	-	-	-	-	-	-	-	VSSA	S	-	-	-	-
20	-	31	-	-	-	-	-	-	-	VREF-	S	-	-	-	-
-	J1	-	K11	K2	19	28	K1	K11	K2	VSSA/ REF-	S	-	-	-	-
21	L1	32	L11	L1	-	29	K2	L11	L1	VREF+	S	-	-	-	VREFBUF_OUT
22	M1	33	L12	L2	-	30	L1	L12	L2	VDDA	S	-	-	-	-
-	-	-	-	-	20	-	-	-	-	VDDA/ REF+	S	-	-	-	-
23	L2	34	J9	K3	21	31	K3	J9	K3	PA0	I/O	FT_a	-	TIM2_CH1, TIM5_CH1, TIM8_ETR, USART2_CTS_NSS, UART4_TX, SAI1_EXTCLK, TIM2_ETR, EVENTOUT	OPAMP1_VIN P, ADC1_IN5, RTC_TAMP2, WKUP1
-	M3	-	-	M1	-	-	-	-	-	OPAMP 1_VINM	I	TT	-	-	-
24	M2	35	K10	N2	22	32	L2	K10	M1	PA1	I/O	FT_I a	-	TIM2_CH2, TIM5_CH2, I2C1_SMBA, SPI1_SCK, USART2_RTS_DE, UART4_RX, OCTOSPIM_P1_DQ S, TIM15_CH1N, EVENTOUT	OPAMP1_VIN M, ADC1_IN6
25	K3	36	H8	N1	23	33	L3	H8	N1	PA2	I/O	FT_I a	-	TIM2_CH3, TIM5_CH3, USART2_TX, LPUART1_TX, OCTOSPIM_P1_NC S, SAI2_EXTCLK, TIM15_CH1, EVENTOUT	ADC1_IN7, WKUP4/LSCO

Table 15. STM32L4Sxxx pin definitions (continued)

Pin Number										Pin name (function after reset)	Pin type	I/O structure	Notes	Alternate functions	Additional functions
STM32L4S5xx STM32L4S7xx					STM32L4S9xx										
LQFP100	BGA132	LQFP144	WLCSP144	UFBGA169	LQFP100	LQFP144	UFBGA144	WLCSP144	UFBGA169						
90	A7	134	C8	A5	92	134	A5	C8	A5	PB4 (NJTRST)	I/O	FT_fa	(4)	NJTRST, TIM3_CH1, I2C3_SDA, SPI1_MISO, SPI3_MISO, USART1_CTS_NSS, UART5_RTS_DE, TSC_G2_IO1, DCMI_D12, SAI1_MCLK_B, TIM17_BKIN, EVENTOUT	COMP2_INP
91	C5	135	E8	B5	93	135	B5	E8	B5	PB5	I/O	FT_Ia	-	LPTIM1_IN1, TIM3_CH2, I2C1_SMBA, SPI1_MOSI, SPI3_MOSI, USART1_CK, UART5_CTS, TSC_G2_IO2, DCMI_D10, COMP2_OUT, SAI1_SD_B, TIM16_BKIN, EVENTOUT	-
92	B5	136	C9	C5	94	136	D5	C9	C5	PB6	I/O	FT_fa	-	LPTIM1_ETR, TIM4_CH1, TIM8_BKIN2, I2C1_SCL, I2C4_SCL, DFSDM1_DATIN5, USART1_TX, TSC_G2_IO3, DCMI_D5, SAI1_FS_B, TIM16_CH1N, EVENTOUT	COMP2_INP

Table 16. Alternate function AF0 to AF7⁽¹⁾

Port		AF0	AF1	AF2	AF3	AF4	AF5	AF6	AF7
		OTG_FS/ SYS_AF	TIM1/2/5/8/L PTIM1	TIM1/2/3/4/ 5	SPI2/SAI1/I2C4/U SART2/OTG_FS/T IM1/8/OCTOSPIM _P1	I2C1/2/3/4/DC MI	SPI1/2/3/I2C4/DFS DM1/DCMI/OCTOS PIM_P1/2	SPI3/I2C3/DFS DM1/COMP1/O CTOSPIM_P2	USART1/2/3
Port A	PA0	-	TIM2_CH1	TIM5_CH1	TIM8_ETR	-	-	-	USART2_CTS_NSS
	PA1	-	TIM2_CH2	TIM5_CH2	-	I2C1_SMBA	SPI1_SCK	-	USART2_RTS_DE
	PA2	-	TIM2_CH3	TIM5_CH3	-	-	-	-	USART2_TX
	PA3	-	TIM2_CH4	TIM5_CH4	SAI1_CK1	-	-	-	USART2_RX
	PA4	-	-	-	OCTOSPIM_P1_NC S	-	SPI1_NSS	SPI3_NSS	USART2_CK
	PA5	-	TIM2_CH1	TIM2_ETR	TIM8_CH1N	-	SPI1_SCK	-	-
	PA6	-	TIM1_BKIN	TIM3_CH1	TIM8_BKIN	DCMI_PIXCLK	SPI1_MISO	-	USART3_CTS_NSS
	PA7	-	TIM1_CH1N	TIM3_CH2	TIM8_CH1N	I2C3_SCL	SPI1_MOSI	-	-
	PA8	MCO	TIM1_CH1	-	SAI1_CK2	-	-	-	USART1_CK
	PA9	-	TIM1_CH2	-	SPI2_SCK	-	DCMI_D0	-	USART1_TX
	PA10	-	TIM1_CH3	-	SAI1_D1	-	DCMI_D1	-	USART1_RX
	PA11	-	TIM1_CH4	TIM1_BKIN2	-	-	SPI1_MISO	-	USART1_CTS_NSS
	PA12	-	TIM1_ETR	-	-	-	SPI1_MOSI	-	USART1_RTS_DE
	PA13	JTMS/SW DIO	IR_OUT	-	-	-	-	-	-
	PA14	JTCK/SW CLK	LPTIM1_OUT	-	-	I2C1_SMBA	I2C4_SMBA	-	-
	PA15	JTDI	TIM2_CH1	TIM2_ETR	USART2_RX	-	SPI1_NSS	SPI3_NSS	USART3_RTS_DE



Table 41. Current consumption in Shutdown mode (continued)

Symbol	Parameter	Conditions		TYP					MAX ⁽¹⁾					Unit
		-	V _{DD}	25°C	55°C	85°C	105°C	125°C	25°C	55°C	85°C	105°C	125°C	
IDD (Shutdown with RTC)	Supply current in Shutdown mode (backup registers retained) RTC enabled	RTC clocked by LSE bypassed at 32768 Hz	1.8 V	245	420	1450	3850	10500	-	-	-	-	-	nA
			2.4 V	340	555	1750	4600	12500	-	-	-	-	-	
			3 V	465	730	2250	5900	15500	-	-	-	-	-	
			3.6 V	615	945	2850	7250	19000	-	-	-	-	-	
		RTC clocked by LSE quartz ⁽²⁾ in low drive mode	1.8 V	335	520	1550	4000	-	-	-	-	-	-	
			2.4 V	435	650	1850	4750	-	-	-	-	-	-	
			3 V	560	830	2350	6050	-	-	-	-	-	-	
			3.6 V	730	1050	2950	7400	-	-	-	-	-	-	
IDD(wakeup from Shutdown)	Supply current during wakeup from Shutdown mode	Wakeup clock is MSI = 4 MHz ⁽³⁾	3 V	0.5	-	-	-	-	-	-	-	-	-	mA

1. Guaranteed by characterization results, unless otherwise specified.

2. Based on characterization done with a 32.768 kHz crystal (MC306-G-06Q-32.768, manufacturer JFVNY) with two 6.8 pF loading capacitors.

3. Wakeup with code execution from Flash. Average value given for a typical wakeup time as specified in [Table 44: Low-power mode wakeup timings](#).

Table 43. Peripheral current consumption (continued)

Peripheral		Range 1 Boost Mode	Range 1 Normal Mode	Range 2	Low-power run and sleep	Unit
AHB (Cont.)	GPIOI	1.6	1.4	1.25	2	µA/MHz
	HASH1	2.6	2.4	2	3	
	OTG_FS independent clock domain	25.5	28	NA	NA	
	OTG_FS AHB clock domain	18	16.5	NA	NA	
	OSPI1 independent clock domain	0.15	0.115	0.084	0.5	
	OSPI1 AHB clock domain	0.665	0.625	0.54	1	
	OSPI1 independent clock domain	2.5	2.4	2.1	2.5	
	OSPI1 AHB clock domain	6.15	5.75	4.6	5.5	
	OSPI2 independent clock domain	1.9	1.65	1.25	1	
	OSPI2 AHB clock domain	5.5	5.25	4.15	5.5	
	RNG independent clock domain	3.9	4.25	NA	NA	
	RNG AHB clock domain	2.65	2.5	NA	NA	
	SDMMC1 independent clock domain	24.5	23.5	NA	NA	
	SDMMC1 AHB clock domain	23.5	22	NA	NA	
	SRAM1	2.65	2.65	2.1	2	
	SRAM2	2.25	2	1.75	2	
	SRAM3	5.35	5	4.25	5.5	
	TSC	1.85	1.75	1.65	1	
	All AHB Peripherals	165	150	125	145	
APB1	AHB to APB1 bridge	0.084	0.25	0.165	0.5	µA/MHz
	CAN1	4.85	4.5	3.75	4.5	
	CRS	0.335	0.25	0.415	0.5	
	DAC1	2.75	2.5	2.1	2.5	
	I2C1 independent clock domain	3.75	3.4	2.9	2.5	

Table 44. Low-power mode wakeup timings⁽¹⁾ (continued)

Symbol	Parameter	Conditions		Typ	Max	Unit
t_{WUSTBY}	Wakeup time from Standby mode to Run mode	Range 1	Wakeup clock MSI = 8 MHz	30.7	47.8	μs
			Wakeup clock MSI = 4 MHz	40.4	55.6	
$t_{WUSTBY\ SRAM2}$	Wakeup time from Standby with SRAM2 to Run mode	Range 1	Wakeup clock MSI = 8 MHz	32.1	49.1	
			Wakeup clock MSI = 4 MHz	41.5	55.5	
t_{WUSHDN}	Wakeup time from Shutdown mode to Run mode	Range 1	Wakeup clock MSI = 4 MHz	265.0	339.4	

1. Guaranteed by characterization results.

Table 45. Regulator modes transition times⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WULPRUN}$	Wakeup time from Low- power run mode to Run mode ⁽²⁾	Code run with MSI 2 MHz	5	7	μs
t_{VOST}	Regulator transition time from Range 2 to Range 1 or Range 1 to Range 2 ⁽³⁾	Code run with MSI 24 MHz	20	40	

1. Guaranteed by characterization results.

2. Time until REGLPF flag is cleared in PWR_SR2.

3. Time until VOSF flag is cleared in PWR_SR2.

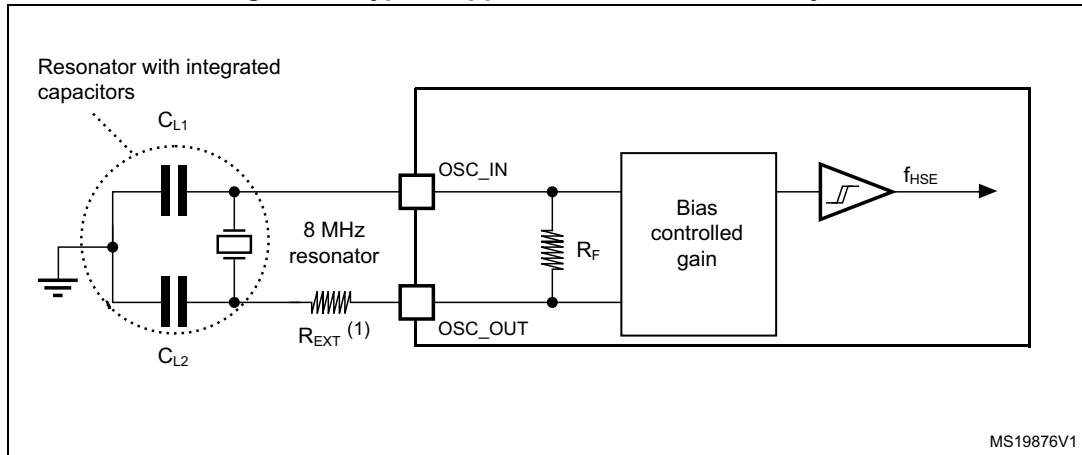
Table 46. Wakeup time using USART/LPUART⁽¹⁾

Symbol	Parameter	Conditions	Typ	Max	Unit
$t_{WUUSART}$ $t_{WULPUART}$	Wakeup time needed to calculate the maximum USART/LPUART baudrate allowing to wakeup up from stop mode when USART/LPUART clock source is HSI	Stop mode 0	-	1.7	μs
		Stop mode 1/2	-	8.5	

1. Guaranteed by characterization results.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

Figure 26. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in [Table 50](#). In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

In the user application, the number of I/O pins which can drive current must be limited to respect the absolute maximum rating specified in [Section 6.2](#):

- The sum of the currents sourced by all the I/Os on V_{DDIOx} , plus the maximum consumption of the MCU sourced on V_{DD} , cannot exceed the absolute maximum rating ΣI_{VDD} (see [Table 19: Voltage characteristics](#)).
- The sum of the currents sunk by all the I/Os on V_{SS} , plus the maximum consumption of the MCU sunk on V_{SS} , cannot exceed the absolute maximum rating ΣI_{VSS} (see [Table 19: Voltage characteristics](#)).

Output voltage levels

Unless otherwise specified, the parameters given in the table below are derived from tests performed under the ambient temperature and supply voltage conditions summarized in [Table 22: General operating conditions](#). All I/Os are CMOS- and TTL-compliant (FT OR TT unless otherwise specified).

Table 68. Output voltage characteristics⁽¹⁾

Symbol	Parameter	Conditions	Min	Max	Unit
V_{OL}	Output low level voltage for an I/O pin	CMOS port ⁽²⁾ $ I_{IO} = 8 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	V
V_{OH}	Output high level voltage for an I/O pin		$V_{DDIOx} - 0.4$	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	TTL port ⁽²⁾ $ I_{IO} = 8 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		2.4	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	$ I_{IO} = 20 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	1.3	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DDIOx} - 1.3$	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	$ I_{IO} = 4 \text{ mA}$ $V_{DDIOx} \geq 1.62 \text{ V}$	-	0.45	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$V_{DDIOx} - 0.45$	-	
$V_{OL}^{(3)}$	Output low level voltage for an I/O pin	$ I_{IO} = 2 \text{ mA}$ $1.62 \text{ V} \geq V_{DDIOx} \geq 1.08 \text{ V}$	-	$0.35 \times V_{DDIOx}$	
$V_{OH}^{(3)}$	Output high level voltage for an I/O pin		$0.65 \times V_{DDIOx}$	-	
$V_{OLFM+}^{(3)}$	Output low level voltage for an FT I/O pin in FM+ mode (FT I/O with "f" option)	$ I_{IO} = 20 \text{ mA}$ $V_{DDIOx} \geq 2.7 \text{ V}$	-	0.4	
		$ I_{IO} = 10 \text{ mA}$ $V_{DDIOx} \geq 1.62 \text{ V}$	-	0.4	
		$ I_{IO} = 2 \text{ mA}$ $1.62 \text{ V} \geq V_{DDIOx} \geq 1.08 \text{ V}$	-	0.4	

1. The I_{IO} current sourced or sunk by the device must always respect the absolute maximum rating specified in [Table 19: Voltage characteristics](#), and the sum of the currents sourced or sunk by all the I/Os (I/O ports and control pins) must always respect the absolute maximum ratings ΣI_{IO} .

Table 78. ADC accuracy - limited test conditions 4⁽¹⁾⁽²⁾⁽³⁾

Sym- bol	Parameter	Conditions ⁽⁴⁾		Min	Typ	Max	Unit
ET	Total unadjusted error	Single ended	Fast channel (max speed)	-	5	5.4	LSB
			Slow channel (max speed)	-	4	5	
		Differential	Fast channel (max speed)	-	4	5	
			Slow channel (max speed)	-	3.5	4.5	
EO	Offset error	Single ended	Fast channel (max speed)	-	2	4	
			Slow channel (max speed)	-	2	4	
		Differential	Fast channel (max speed)	-	2	3.5	
			Slow channel (max speed)	-	2	3.5	
EG	Gain error	Single ended	Fast channel (max speed)	-	4	4.5	
			Slow channel (max speed)	-	4	4.5	
		Differential	Fast channel (max speed)	-	3	4	
			Slow channel (max speed)	-	3	4	
ED	Differential linearity error	Single ended	Fast channel (max speed)	-	1	1.5	
			Slow channel (max speed)	-	1	1.5	
		Differential	Fast channel (max speed)	-	1	1.2	
			Slow channel (max speed)	-	1	1.2	
EL	Integral linearity error	Single ended	Fast channel (max speed)	-	2.5	3	
			Slow channel (max speed)	-	2.5	3	
		Differential	Fast channel (max speed)	-	2	2.5	
			Slow channel (max speed)	-	2	2.5	
ENOB	Effective number of bits	Single ended	Fast channel (max speed)	10.2	10.5	-	bits
			Slow channel (max speed)	10.2	10.5	-	
		Differential	Fast channel (max speed)	10.6	10.7	-	
			Slow channel (max speed)	10.6	10.7	-	
SINAD	Signal-to-noise and distortion ratio	Single ended	Fast channel (max speed)	63	65	-	dB
			Slow channel (max speed)	63	65	-	
		Differential	Fast channel (max speed)	65	66	-	
			Slow channel (max speed)	65	66	-	
SNR	Signal-to-noise ratio	Single ended	Fast channel (max speed)	64	65	-	
			Slow channel (max speed)	64	65	-	
		Differential	Fast channel (max speed)	66	67	-	
			Slow channel (max speed)	66	67	-	

6.3.26 Temperature sensor characteristics

Table 84. TS characteristics

Symbol	Parameter	Min	Typ	Max	Unit
$T_L^{(1)}$	V_{TS} linearity with temperature	-	± 1	± 2	$^{\circ}\text{C}$
Avg_Slope ⁽²⁾	Average slope	2.3	2.5	2.7	mV/ $^{\circ}\text{C}$
V_{30}	Voltage at 30 $^{\circ}\text{C}$ ($\pm 5^{\circ}\text{C}$) ⁽³⁾	0.742	0.76	0.785	V
$t_{\text{START}}^{(1)}$ (TS_BUF) ⁽¹⁾	Sensor Buffer Start-up time in continuous mode ⁽⁴⁾	-	8	15	μs
$t_{\text{START}}^{(1)}$	Start-up time when entering in continuous mode ⁽⁴⁾	-	70	120	μs
$t_{\text{S_temp}}^{(1)}$	ADC sampling time when reading the temperature	5	-	-	μs
$I_{\text{DD}}(\text{TS})^{(1)}$	Temperature sensor consumption from V_{DD} , when selected by ADC	-	4.7	7	μA

1. Guaranteed by design.
2. Guaranteed by characterization results.
3. Measured at $V_{\text{DDA}} = 3.0 \text{ V} \pm 10 \text{ mV}$. The V_{30} ADC conversion result is stored in the TS_CAL1 byte. Refer to [Table 8: Temperature sensor calibration values](#).
4. Continuous mode means Run/Sleep modes, or temperature sensor enable in Low-power run/Low-power sleep modes.

6.3.27 V_{BAT} monitoring characteristics

Table 85. V_{BAT} monitoring characteristics

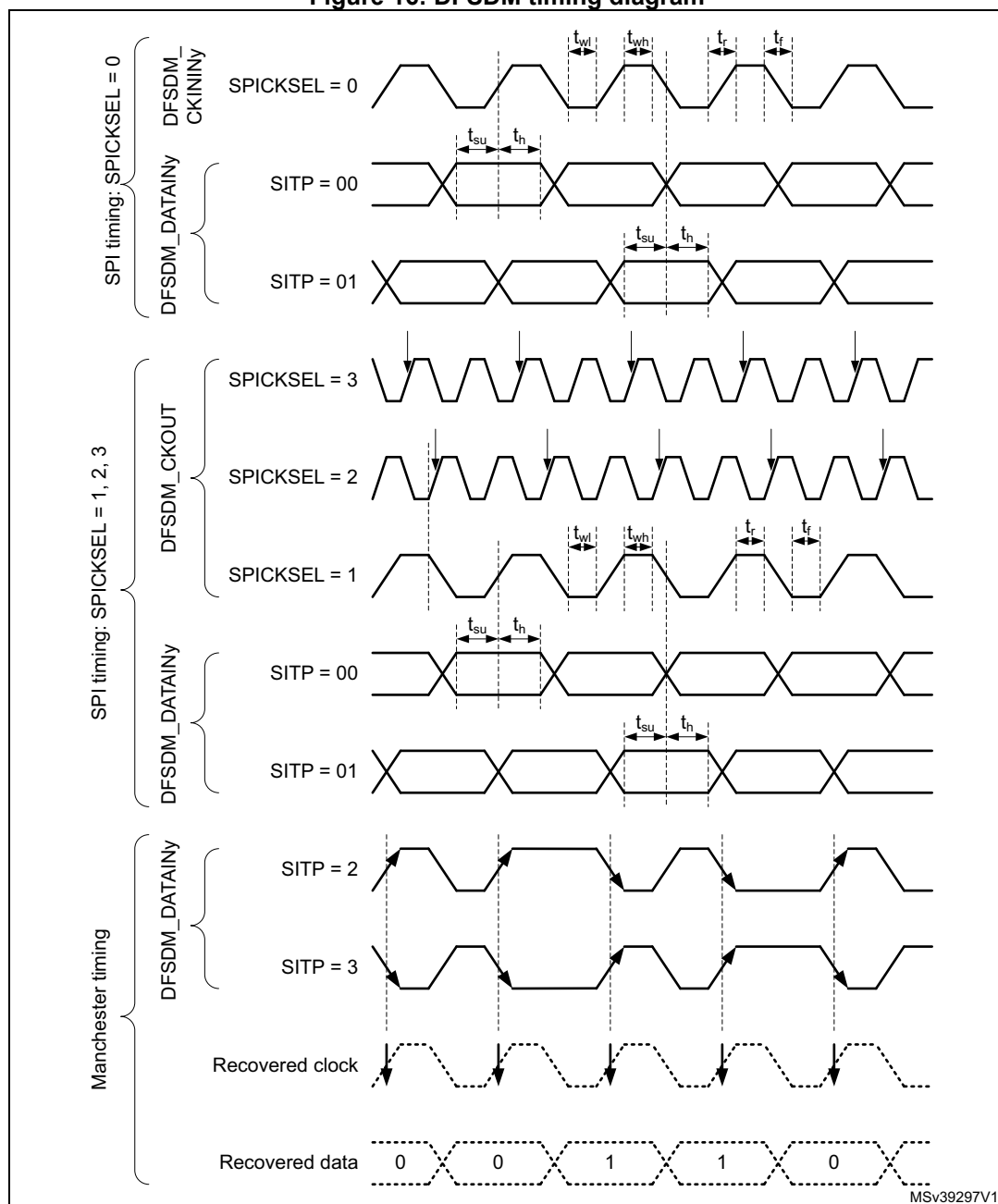
Symbol	Parameter	Min	Typ	Max	Unit
R	Resistor bridge for V_{BAT}	-	39	-	k Ω
Q	Ratio on V_{BAT} measurement	-	3	-	-
$E_r^{(1)}$	Error on Q	-10	-	10	%
$t_{\text{S_vbat}}^{(1)}$	ADC sampling time when reading the VBAT	12	-	-	μs

1. Guaranteed by design.

Table 86. V_{BAT} charging characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{BC}	Battery charging resistor	VBRS = 0	-	5	-	k Ω
		VBRS = 1	-	1.5	-	

Figure 16: DFSDM timing diagram



6.3.29 Timer characteristics

The parameters given in the following tables are guaranteed by design.

Refer to [Section 6.3.17: I/O port characteristics](#) for details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output).

SAI characteristics

Unless otherwise specified, the parameters given in [Table 93](#) for SAI are derived from tests performed under the ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in [Table 22: General operating conditions](#), with the following configuration:

- Output speed is set to $\text{OSPEEDRy}[1:0] = 10$
- Capacitive load $C = 30 \text{ pF}$
- Measurement points are done at CMOS levels: $0.5 \times V_{\text{DD}}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CK,SD,FS).

Table 96. USB BCD DC electrical characteristics⁽¹⁾ (continued)

Driver characteristics						
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
VLGC	Logic threshold	-	0.8	-	2.0	V
VDAT_REF	Data detect voltage	-	0.25	-	0.4	V
VDP_SRC	D+ source voltage	-	0.5	-	0.7	V
VDM_SRC	D- source voltage	-	0.5	-	0.7	V
IDP_SINK	D+ sink current	-	25	-	175	μA
IDM_SINK	D- sink current	-	25	-	175	μA

1. Guaranteed by design

CAN (controller area network) interface

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

6.3.31 FSMC characteristics

Unless otherwise specified, the parameters given in [Table 97](#) to [Table 110](#) for the FMC interface are derived from tests performed under the ambient temperature, f_{HCLK} frequency and V_{DD} supply voltage conditions summarized in [Table 22](#), with the following configuration:

- Output speed is set to $OSPEEDRy[1:0] = 11$
- Capacitive load $C = 30$ pF
- Measurement points are done at CMOS levels: $0.5 \times V_{DD}$

Refer to [Section 6.3.17: I/O port characteristics](#) for more details on the input/output characteristics.

Asynchronous waveforms and timings

[Figure 45](#) through [Figure 48](#) represent asynchronous waveforms and [Table 97](#) through [Table 104](#) provide the corresponding timings. The results shown in these tables are obtained with the following FMC configuration:

- AddressSetupTime = 0x1
- AddressHoldTime = 0x1
- DataHoldTime = 0x1
- ByteLaneSetup = 0x1
- DataSetupTime = 0x1 (except for asynchronous NWAIT mode, DataSetupTime = 0x5)
- BusTurnAroundDuration = 0x0

In all timing tables, the THCLK is the HCLK clock period.

7 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

7.1 UFBGA169 package information

Figure 67. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package outline

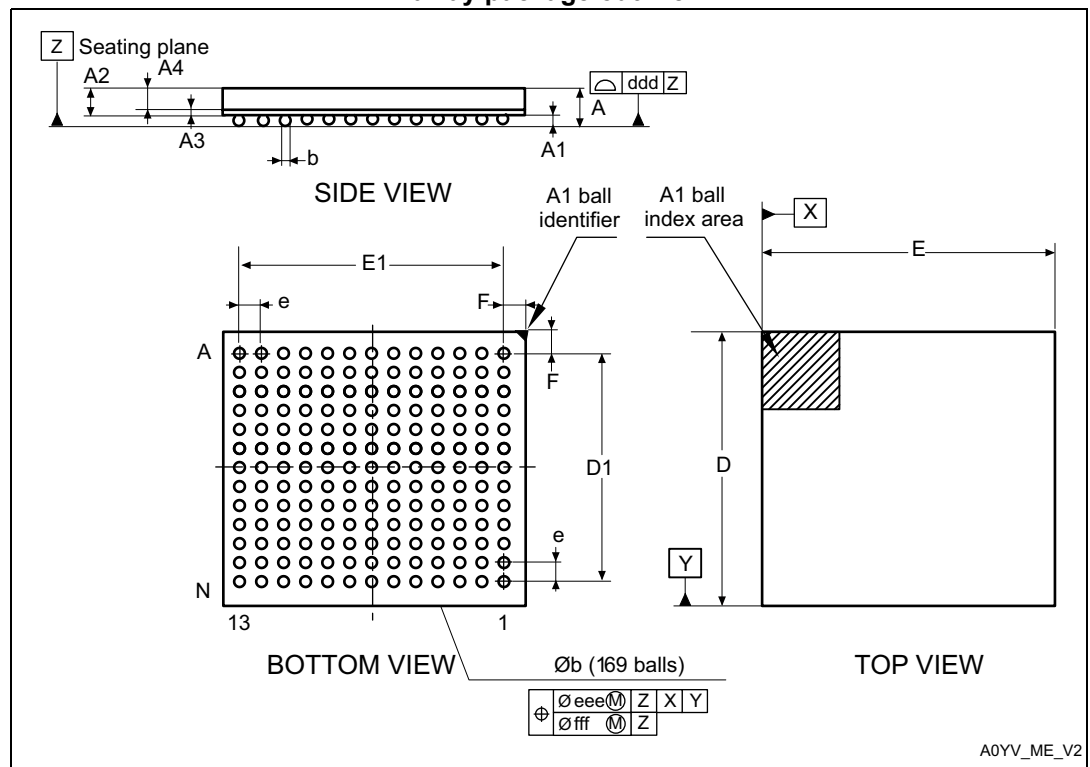


Table 118. UFBGA169 - 169-ball, 7 x 7 mm, 0.50 mm pitch, ultra fine pitch ball grid array package mechanical data

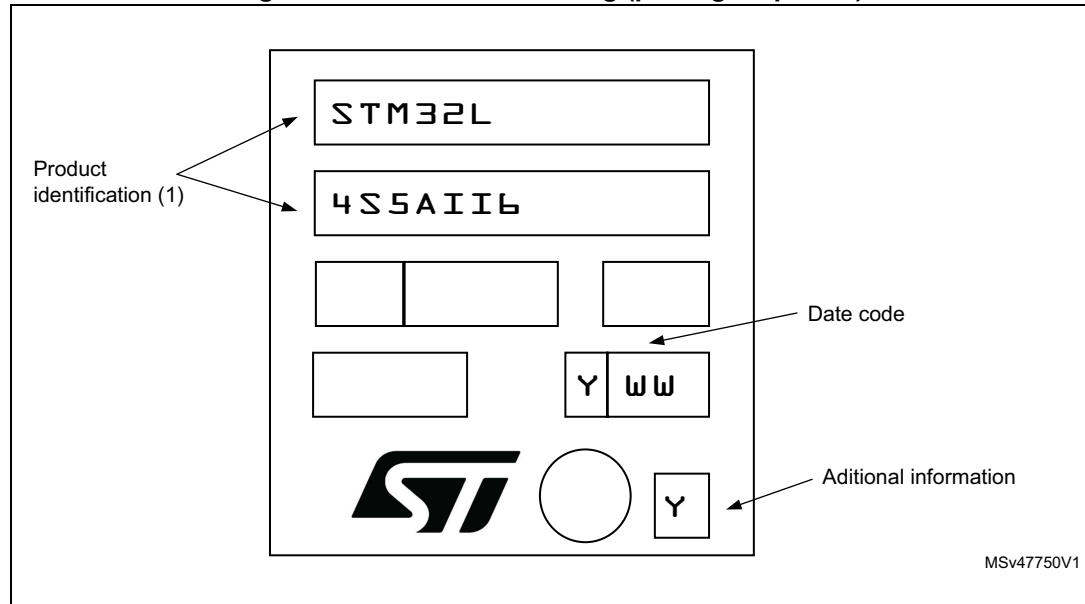
Symbol	millimeters			inches ⁽¹⁾		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	0.460	0.530	0.600	0.0181	0.0209	0.0236
A1	0.050	0.080	0.110	0.0020	0.0031	0.0043
A2	0.400	0.450	0.500	0.0157	0.0177	0.0197
A3	-	0.130	-	-	0.0051	-
A4	0.270	0.320	0.370	0.0106	0.0126	0.0146

UFBGA169 device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 69. UFBGA169 marking (package top view)



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.